TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# 2SC5464FT

#### VHF~UHF Band Low Noise Amplifier Applications

• Low noise figure, high gain.

• NF = 1.1dB,  $|S_{21e}|^2 = 12dB$  (f = 1 GHz)

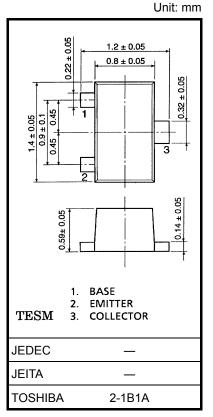
# Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	20	V
Collector-emitter voltage	$V_{CEO}$	12	V
Emitter-base voltage	$V_{EBO}$	3	V
Collector current	IC	60	mA
Base current	lΒ	30	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	<b>−55~125</b>	°C

Note:

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions","Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.0022 g (typ.)

# Microwave Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 8 V, I <sub>C</sub> = 15 mA	5	7	_	GHz
Insertion gain -	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 500 \text{ MHz}$	-	17.5	_	- dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 8 \text{ V}, I_{C} = 15 \text{ mA}, f = 1 \text{ GHz}$	8	12	_	
Noise figure -	NF (1)	$V_{CE} = 8 \text{ V}, I_{C} = 5 \text{ mA}, f = 500 \text{ MHz}$	_	1	_	- dB
	NF (2)	$V_{CE} = 8 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	-	1.1	2	

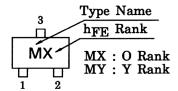
## **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	$V_{EB} = 1 \text{ V}, I_{C} = 0$	1	_	1	μΑ
DC current gain	h <sub>FE</sub> (Note 1)	V <sub>CE</sub> = 8 V, I <sub>C</sub> = 15 mA	80	_	240	
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 8 V, I <sub>E</sub> = 0, f = 1 MHz (Note 2)	_	0.75	_	pF
Reverse transfer capacitance	C <sub>re</sub>	VCB = 0 V, $IE = 0$ , $I = 1$ WIFZ (NOTE 2)	_	0.5	_	pF

Note 1: hFF classification O: 80~160, Y: 120~240

Note 2: Cre is measured by 3 terminal method with capacitance bridge.

# Marking



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20070701-EN GENERAL

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